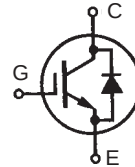


NPT³ IGBT with Diode in ISOPLUS 247™

IXER 35N120D1

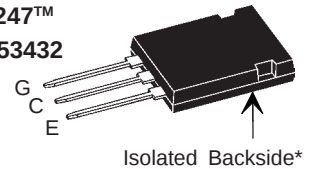
$$\begin{aligned} I_{C25} &= 50 \text{ A} \\ V_{CES} &= 1200 \text{ V} \\ V_{CE(sat)typ.} &= 2.2 \text{ V} \end{aligned}$$



ISOPLUS 247™



E153432



Isolated Backside*

G = Gate C = Collector E = Emitter

*Patent pending

IGBT

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	1200	V
V_{GES}		± 20	V
I_{C25}	$T_C = 25^{\circ}\text{C}$	50	A
I_{C90}	$T_C = 90^{\circ}\text{C}$	32	A
I_{CM} V_{CEK}	$V_{GE} = \pm 15 \text{ V}; R_G = 39 \Omega; T_{VJ} = 125^{\circ}\text{C}$ RBSOA, Clamped inductive load; $L = 100 \mu\text{H}$	50 V_{CES}	A
t_{SC} (SCSOA)	$V_{CE} = 900\text{V}; V_{GE} = \pm 15 \text{ V}; R_G = 39 \Omega; T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10	μs
P_{tot}	$T_C = 25^{\circ}\text{C}$	200	W

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{CE(sat)}$	$I_C = 35 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	2.2 2.6		V V
$V_{GE(th)}$	$I_C = 1 \text{ mA}; V_{GE} = V_{CE}$	4.5		6.5 V
I_{CES}	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	0.4		0.4 mA mA
I_{GES}	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$			200 nA
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 600 \text{ V}; I_C = 35 \text{ A}$ $V_{GE} = \pm 15 \text{ V}; R_G = 39 \Omega$	150 60 700 50		ns ns ns ns
		4.2 3.5		mJ mJ
C_{ies}		2		nF
Q_{Gon}		250		nC
R_{thJC} R_{thJH}		1.2		0.6 K/W K/W

Features

- NPT³ IGBT
 - low saturation voltage
 - positive temperature coefficient for easy paralleling
 - fast switching
 - short tail current for optimized performance in resonant circuits
- HiPerFRED™ diode
 - fast reverse recovery
 - low operating forward voltage
 - low leakage current
- ISOPLUS 247™ package
 - isolated back surface
 - low coupling capacity between pins and heatsink
 - high reliability
 - industry standard outline

Applications

- single switches
- choppers with complementary free wheeling diodes
- phaselegs, H bridges, three phase bridges e.g. for
 - power supplies, UPS
 - AC, DC and SR drives
 - induction heating

Diode

Symbol	Conditions	Maximum Ratings	
I_{F25}	$T_C = 25^\circ\text{C}$	48	A
I_{F90}	$T_C = 90^\circ\text{C}$	25	A

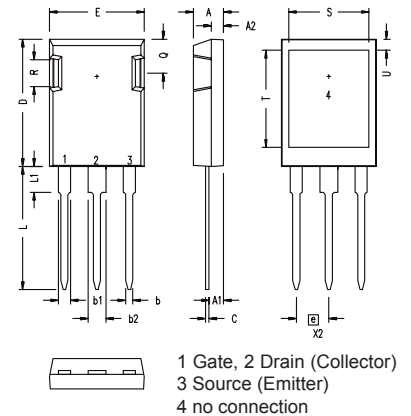
Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_F	$I_F = 35\text{ A}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	2.5 1.9	2.9	V V
I_{RM} t_{rr}	$I_F = 30\text{ A}; di_F/dt = -500\text{ A}/\mu\text{s}; T_{VJ} = 125^\circ\text{C}$ $V_R = 600\text{ V}; V_{GE} = 0\text{ V}$	27 150		A ns
R_{thJC} R_{thJH}	(per diode)	2.6		1.3 K/W K/W

Component

Symbol	Conditions	Maximum Ratings	
T_{VJ} T_{stg}		-55...+150 -55...+125	$^\circ\text{C}$ $^\circ\text{C}$
V_{ISOL}	$I_{ISOL} \leq 1\text{ mA}; 50/60\text{ Hz}$	2500	V~
F_c	mounting force with clip	20...120	N

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
C_p	coupling capacity between shorted pins and mounting tab in the case		30	pF
Weight			6	g

ISOPLUS 247 OUTLINE



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	.244
R	4.32	4.83	.170	.190
S	13.21	13.72	.520	.540
T	15.75	16.26	.620	.640
U	1.65	3.03	.065	.080